Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
30V	6mΩ@10V	35A
	9.4mΩ@4.5V	

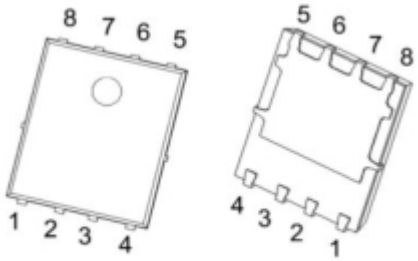
Feature

- Fast Switching
- Low Gate Charge and Rdson
- Low Reverse transfer capacitances
- 100% Single Pulse avalanche energy Test

Application

- Power switching application
- Isolated DC/DC Converters in Telecom and Industrial

Package



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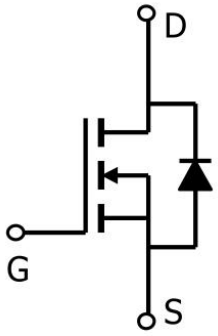
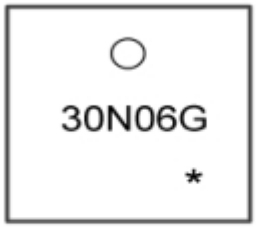
Circuit diagram



Marking



30N06G **=Device Code**
***** **=Month Code**

Absolute maximum ratings

(T_a=25℃ unless otherwise noted)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Continuous Drain Current, VGS @ 10V [1]	I_D@T_C=25℃	35	A
Pulsed Drain Current[2]	I_{DM}	140	A
Single Pulse Avalanche Energy [3]	E_{AS}	39.2	mJ
Avalanche Current	I_{AS}	28	A
Total Power Dissipation [4]	P_D@T_C=25℃	28	W
Thermal Resistance Junction-Case [1]	$R_{\theta JC}$	4.5	℃/W
Storage Temperature Range	T_{STG}	-55 to 150	℃
Operating Junction Temperature Range	T_J	-55 to 150	℃

Electrical characteristics

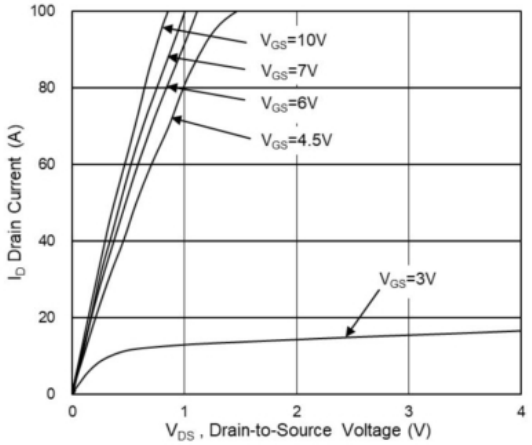
(T_A=25℃, unless otherwise noted)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
Drain-Source Breakdown Voltage	$BV_{(BR)DSS}$	V_{GS} = 0V, I_D =250μA	30			V
Drain-Source Leakage Current	I_{DSS}	V_{DS} =30V, V_{GS} = 0V, T_J=25℃			1	uA
Drain-Source Leakage Current	I_{DSS}	V_{DS} =30V, V_{GS} = 0V, T_J=55℃			5	uA
Gate-Source Leakage Current	I_{GSS}	V_{DS} =0V,V_{GS} =±20V			±100	uA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} =V_{GS}, I_D =250μA	1.2	1.7	2.2	V
Static Drain-Source On-Resistance[2]	$R_{DS(on)}$	V_{GS} =10V, I_D =12A		6	8	mΩ
		V_{GS} =4.5V, I_D =12A		9.4	11	
Gate Threshold Voltage	R_g	V_{DS}=0V, V_{GS}=0V, f=1MHz	0.8	1.7	2.6	Ω
Dynamic Characteristics						
Forward Transconductance	g_{fs}	V_{DS} =5V, I_D =12A		55		S
Total Gate Charge (4.5V)	Q_g	V_{DS}=15V, V_{GS}=10V, I_D =12A		7.1		pF
Gate-Source Charge	Q_{gs}			2.2		
Gate-Drain Charge	Q_{gd}			3.1		
Input Capacitance	C_{iss}	V_{DS}=15V, V_{GS}=0V, f=1MHz		693		pF
Output Capacitance	C_{oss}			332		
Reverse Transfer Capacitance	C_{rss}			34		
Switching Characteristics[4]						
Turn-On Delay Time	$T_{d(on)}$	V_{DD}=15V, V_{GS}=10V, R_G=3Ω, I_D =12A		7		nS
Rise Time	T_r			18.8		
Turn-Off Delay Time	$T_{d(off)}$			19.5		
Fall Time	T_f			3.4		
Drain-Source Diode Characteristics						
Continuous Source Current[1,5]	I_S	V_G=V_D=0V , Force Current			12	A
Diode Forward Voltage[2]	V_{SD}	V_{GS}=0V , I_S=1A , T_J=25℃			1	V

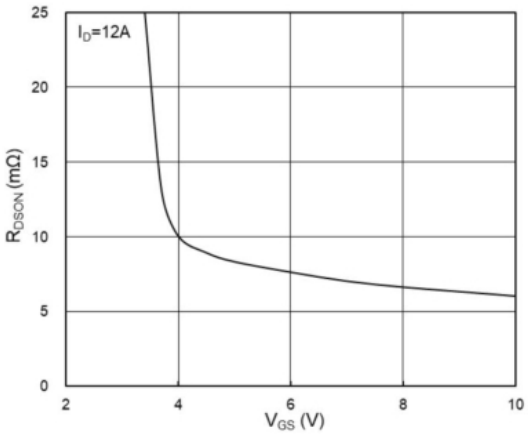
Notes:

1. The data tested by surface mounted on a 1 inch2 FR-4 board with 2OZ copper.
2. The data tested by pulsed , pulse width ≦ 300us , duty cycle ≦ 2%
3. The EAS data shows Max. rating . The test condition is V_{DD}=25V,V_{GS}=10V,L=0.1mH,I_{AS}=28A
4. The power dissipation is limited by 150℃ junction temperature
5. The data is theoretically the same as I_D and I_{DM} , in real applications , should be limited by total power dissipation.

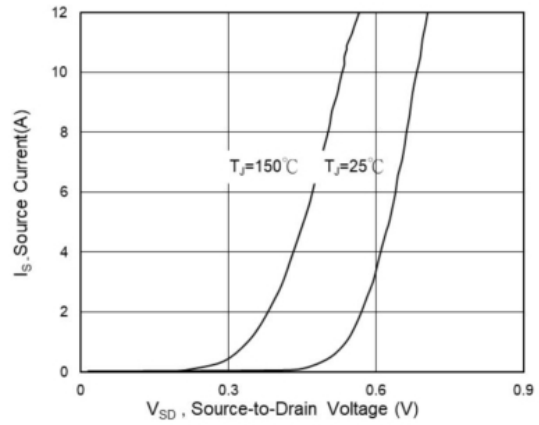
Typical Characteristics



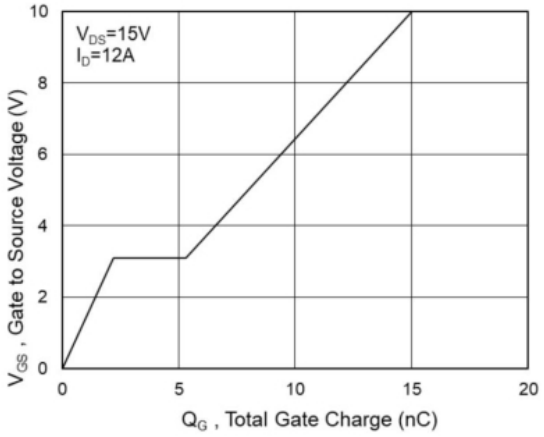
Typical Output Characteristics



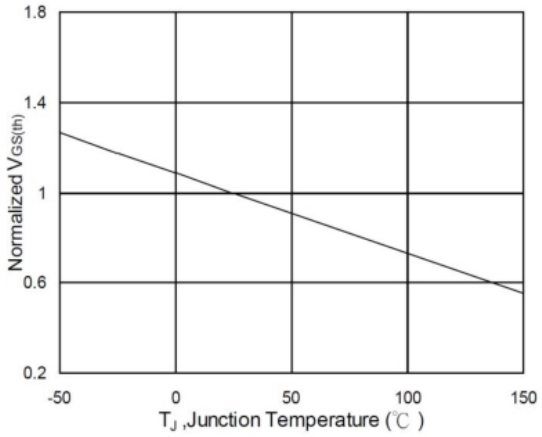
On-Resistance vs G-S Voltage



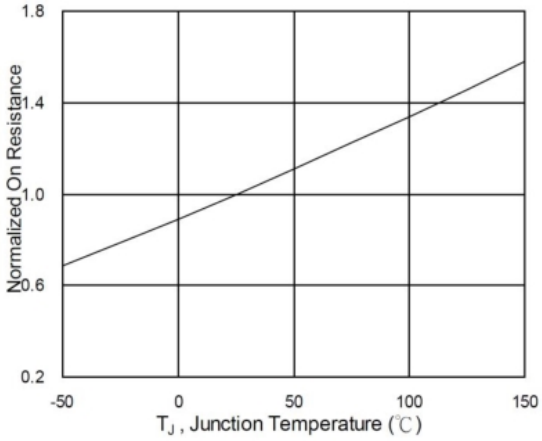
Source Drain Forward Characteristics



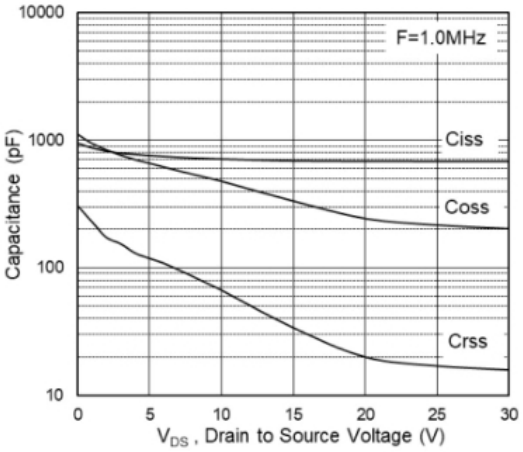
Gate-Charge Characteristics



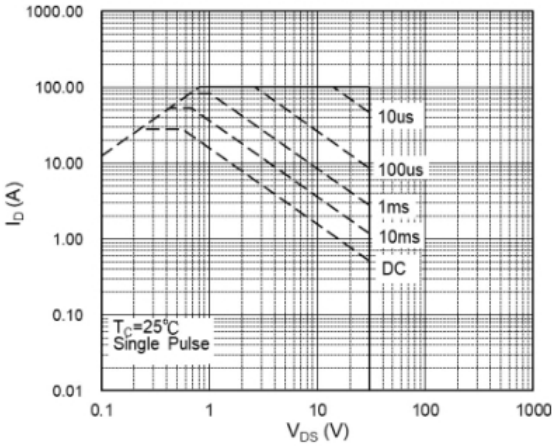
Normalized $V_{GS(th)}$ vs T_J



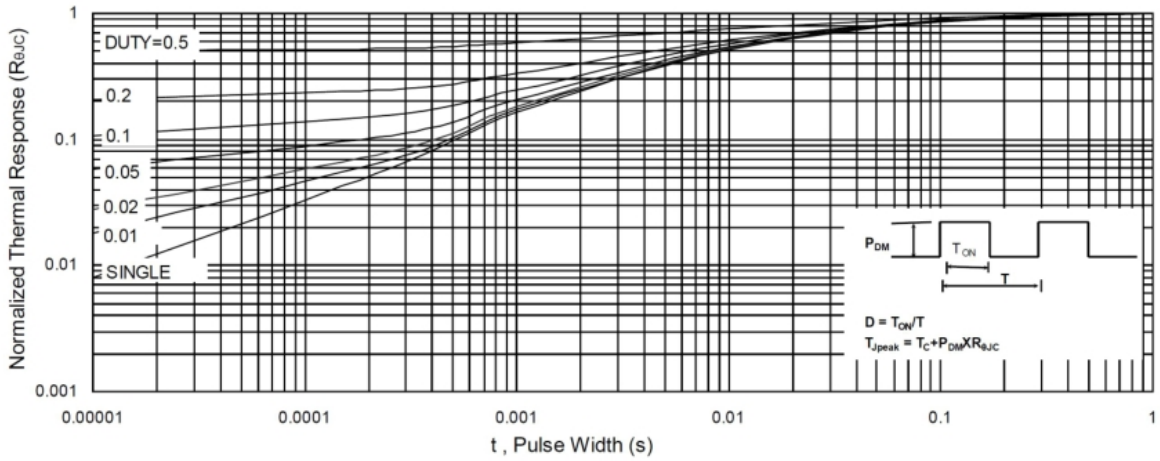
Normalized R_{DSON} vs T_J



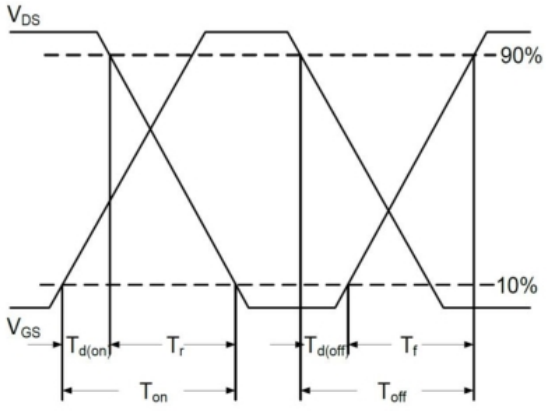
Capacitance



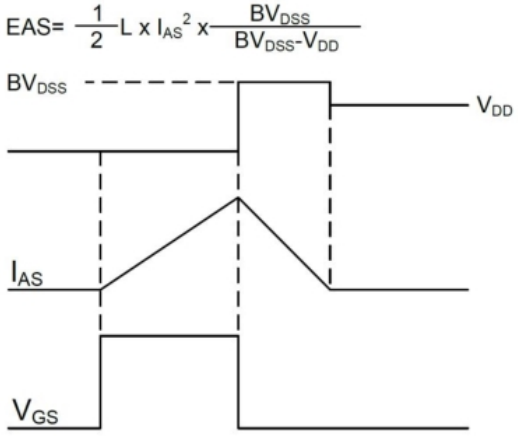
Safe Operating Area



Normalized Maximum Transient Thermal Impedance

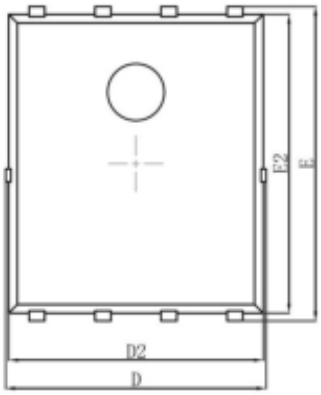


Switching Time Waveform

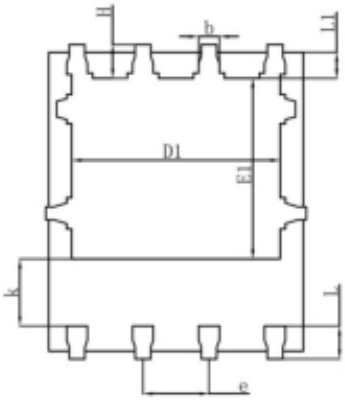


Unclamped Inductive Switching Waveform

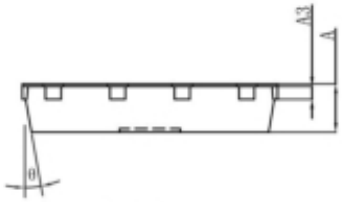
PDFN5X6-8L Package Information



Top View
[顶视图]



Bottom View
[背视图]



Side View
[侧视图]

Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.000	0.035	0.039
A3	0.254REF.		0.010REF.	
D	4.944	5.096	0.195	0.201
E	5.974	6.126	0.235	0.241
D1	3.910	4.110	0.154	0.162
E1	3.375	3.575	0.133	0.141
D2	4.824	4.976	0.190	0.196
E2	5.674	5.826	0.223	0.229
k	1.190	1.390	0.047	0.055
b	0.350	0.450	0.014	0.018
e	1.270TYP.		0.050TYP.	
L	0.559	0.711	0.022	0.028
L1	0.424	0.576	0.017	0.023
H	0.574	0.726	0.023	0.029
θ	10°	12°	10°	12°